

Rewrite claim 3 as follows:

Sub D1
C2
3. (Twice Amended) A semiconductor device in which a plurality of semiconductor elements are formed on a substrate, wherein
in at least semiconductor elements, among said plurality of semiconductor elements, that samples data to be supplied to other semiconductor elements, a channel width of a channel region formed in a semiconductor layer to which laser annealing is applied is larger than a channel length thereof, a channel width direction is formed in a direction different from a major-axis direction and a minor-axis direction of a laser-beam irradiated region at the time of application of said laser annealing, and a channel width direction is neither vertical nor parallel with regard to at least two different major side directions of said substrate.

Rewrite claim 5 as follows:

Sub D1
C3
5. (Twice Amended) A display device, comprising:
a plurality of pixel electrodes arranged on a substrate;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating pixels to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive circuit for supplying display signals to said plurality of first thin-film transistors, wherein
in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said first thin-film transistors, a channel width of a channel region formed in a semiconductor film to which laser annealing is applied is larger than a channel length thereof, a channel width direction is neither vertical to nor parallel with regard to a side direction of said substrate.

Rewrite claim 9 as follows:

- Sub D1
- C4
9. (Twice Amended) A display device, comprising:
a plurality of pixel electrodes arranged on a substrate;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating pixels to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive circuit for supplying display signals to said plurality of first thin-film transistors, wherein
in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said first-thin film transistors, a channel width of a channel region formed in a semiconductor film to which laser annealing is applied is larger than a channel length thereof, and a channel width direction is formed in a direction different from a side direction of said substrate, and
said channel width direction of said some or all of second thin-film transistors is set to a direction of about 45° relative to any one or all of a plurality of side directions of said substrate.

Rewrite claim 10 as follows:

- Sub D1
- C5
10. (Twice Amended) A display device, comprising:
a plurality of pixel electrodes arranged on a substrate;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating pixels to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive

circuit for supplying display signals to said plurality of first thin-film transistors, wherein

in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said first-thin film transistors, a channel width of a channel region formed in a semiconductor film to which laser annealing is applied is larger than a channel length thereof, and a channel width direction is formed in a direction different from a major-axis direction and a minor-axis direction of a laser-beam irradiated region at the time of application of said laser annealing.

Rewrite claim 14 as follows:

C5
C6
Sub D1
14. (Twice Amended) A display device, comprising:
a plurality of pixel electrodes arranged on a substrate;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating pixels to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive circuit for supplying display signals to said plurality of first thin-film transistors, wherein

in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said first-thin transistors, a channel width of a channel region formed in a semiconductor film to which laser annealing is applied is larger than a channel length thereof, and a channel width direction is formed in a direction different from a major-axis direction and/or a minor-axis direction of a laser-beam irradiated region at the time of application of said laser annealing, and

said channel width direction of said some or all of second thin-film transistors is set to a direction of about 45° relative to the major-axis direction and/or the minor-axis direction of said laser-beam irradiated region.

Rewrite claim 17 as follows:

Sub D1
17. (Twice Amended) A liquid crystal display device, comprising:
a plurality of pixel electrodes arranged on one of a pair of substrates holding a liquid crystal therebetween;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating the liquid crystal to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive circuit for supplying display signals to said plurality of first thin-film transistors, channel regions of said plurality of first and second thin-film transistors being formed in a semiconductor film to which laser annealing is applied, and
C7
cm+ in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said first thin-film transistors, a channel width being larger than a channel length, and a channel width direction of some or all of second thin-film transistors being formed non-parallel with and non-orthogonal to a channel width direction of said first thin-film transistors,
wherein
among said plurality of second thin-film transistors, said some or all of second thin-film transistors in which the channel width direction is formed non-parallel with and non-orthogonal to the channel width direction of said first thin-film transistors
are used, in said display drive circuit, as sampling transistors for sampling video signals at a predetermined timing and supplying said display signals to the corresponding plurality of first thin-film transistors.

Rewrite claim 18 as follows:

C7
CMT

18. (Twice Amended) A liquid crystal display device, comprising:
a plurality of pixel electrodes arranged on one of a pair of substrates holding a liquid crystal therebetween;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating the liquid crystal to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive circuit for supplying display signals to said plurality of first thin-film transistors,
channel regions of said plurality of first and second thin-film transistors being formed in a semiconductor film to which laser annealing is applied, and
in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said first-thin film transistors, a channel width being larger than a channel length, a channel width direction of some or all of second thin-film transistors being formed non-parallel with and non-orthogonal to a channel width direction of said first thin-film transistors, and a channel width is larger than a channel length and a channel width direction differs from the direction of the sides of the substrate and from a channel width direction of the first-thin film transistors in at least the sampling transistors among the second thin-film transistors,
wherein
said display drive circuit comprises:
a video signal line to which the video signals are supplied from outside, sampling transistors for sampling the video signals from said video signal line at a predetermined timing and supplying said display signals to the corresponding plurality of first thin-film transistors, and a shift register for controlling switching operation of said sampling transistors,

C7 added
and wherein, among said plurality of second thin-film transistors, said some or all of second thin-film transistors in which the channel width direction is formed non-parallel with and non-orthogonal to the channel width direction of said first thin-film transistors

are used in said sampling transistors and the shift register.

Rewrite claim 20 as follows:

Sub D1
C8 CMT
20. (Twice Amended) A liquid crystal display device, comprising:
a plurality of pixel electrodes arranged on one of a pair of substrates holding a liquid crystal therebetween;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating the liquid crystal to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive circuit for supplying display signals to said plurality of first thin-film transistors,
channel regions of said plurality of first and second thin-film transistors being formed in a semiconductor film to which laser annealing is applied, and
in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said thin-film transistors, a channel width being larger than a channel length, and a channel width direction of some or all of second thin-film transistors being formed non-parallel with and non-orthogonal to a channel width direction of said first thin-film transistors,
wherein
said channel width direction of the channel region of said some or all of second thin-film transistors is set to a direction of about 45° relative to the channel width direction of said first thin-film transistors.

Rewrite claim 21 as follows:

Sub D1
21. (Twice Amended) A display device, comprising:
a plurality of pixel electrodes arranged on a substrate;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating pixels to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive circuit for supplying display signals to said plurality of first thin-film transistors, wherein
C9 cm+ in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said first thin-film transistors, a channel width of a channel region formed in a semiconductor film to which laser annealing is applied is larger than a channel length thereof, and a channel width direction is formed in a direction different from a major-axis direction and/or a minor-axis direction of a laser-beam irradiated region at the time of application of said laser annealing, and
the channel width of some or all of said plurality of second thin-film transistors is formed neither parallel with nor orthogonal to a channel width direction of said plurality of first thin-film transistors.

Rewrite claim 22 as follows:

22. (Twice Amended) A display device, comprising:
a plurality of pixel electrodes arranged on a substrate;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating pixels to the connected pixel electrodes; and
a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive

circuit for supplying display signals to said plurality of first thin-film transistors,
wherein

in at least transistors, among said plurality of second thin-film transistors, that sample display data to be supplied to said first-thin film transistors, a channel width of a channel region formed in a semiconductor film to which laser annealing is applied is larger than a channel length thereof, a channel width direction is formed in a direction different from a major-axis direction and/or a minor-axis direction of a laser-beam irradiated region at the time of application of said laser annealing, and a channel width is larger than a channel length and a channel width direction differs from the direction of the size of the substrate and from a channel width direction of the first-thin film transistors than at least the sampling transistors among the second thin-film transistors,

the channel width of some or all of said plurality of second thin-film transistors is formed neither parallel with nor orthogonal to a channel width direction of said plurality of first thin-film transistors, and

said display drive circuit comprises:

a video signal line to which the video signals are supplied from outside, sampling transistors for sampling the video signals from said video signal line at a predetermined timing and supplying said display signals to the corresponding plurality of first thin-film transistors, and a shift register for controlling switching operation of said sampling transistors,

and wherein, among said plurality of second thin-film transistors, said some or all of second thin-film transistors in which the channel width is larger than the channel length and the channel width direction is formed in a direction different from the major-axis direction and/or the minor-axis direction of said laser beam irradiated region are used in said sampling transistors and the shift register.

Please add the following new claim:

Sub DI
C-10
--23. (New) A display device, comprising:

a plurality of pixel electrodes arranged on a substrate;
a plurality of first thin-film transistors connected to corresponding pixel electrodes among said plurality of pixel electrodes for supplying signals for operating pixels to the connected pixel electrodes; and

a plurality of second thin-film transistors constituting a scanning drive circuit for scanning said plurality of first thin-film transistors and/or a display drive circuit for supplying display signals to said plurality of first thin-film transistors, wherein

in at least transistors, among said plurality of second thin-film transistors, that samples display data to be supplied to said first-thin film transistors, a channel width of a channel region formed in a semiconductor film to which laser annealing is applied is larger than a channel length thereof, a channel width direction is neither vertical to nor parallel with regard to a side direction of said substrate, and said channel width direction is formed in a direction different from a major-axis direction and a minor-axis direction of a laser-beam irradiated region at the time of application of said laser annealing. --